UP04401

Silicon PNP epitaxial planar type

For general amplification

■ Features

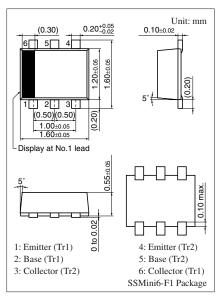
- Two elements incorporated into one package (Each transistor is separated)
- Reduction of the mounting area and assembly cost by one half

■ Basic Part Number

• 2SB0709A × 2

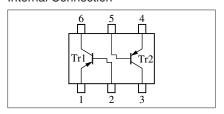
■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-60	V	
Collector-emitter voltage (Base open)	V _{CEO}	-50	V	
Emitter-base voltage (Collector open)	V_{EBO}	-7	V	
Collector current	I_C	-100	mA	
Peak collector current	I_{CP}	-200	mA	
Total power dissipation	P_{T}	125	mW	
Junction temperature	T_{j}	125	°C	
Storage temperature	T_{stg}	-55 to +125	°C	



Marking Symbol: 5K

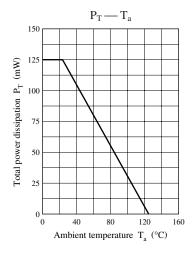
Internal Connection

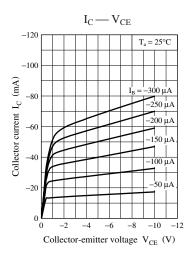


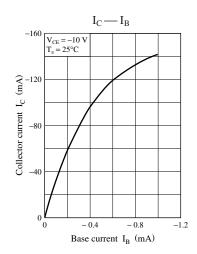
■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

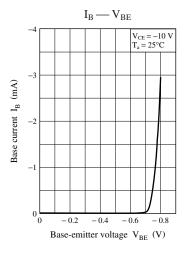
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_C = -10 \mu A, I_E = 0$	-60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = -2 \text{ mA}, I_B = 0$	-50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \ \mu A, I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -20 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = -10 \text{ V}, I_B = 0$			-100	μΑ
Forward current transfer ratio	h_{FE}	$V_{CE} = -10 \text{ V}, I_{C} = -2 \text{ mA}$	180		390	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$		- 0.3	- 0.5	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		2.7		pF
(Common base, input open circuited)						

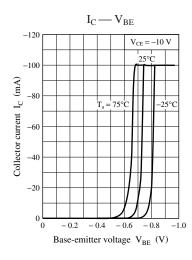
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

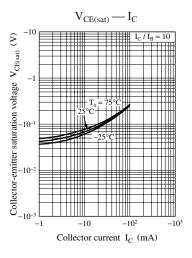


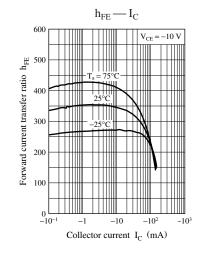


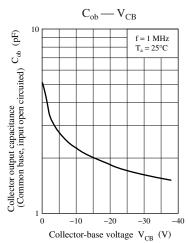












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